

FIG. 1

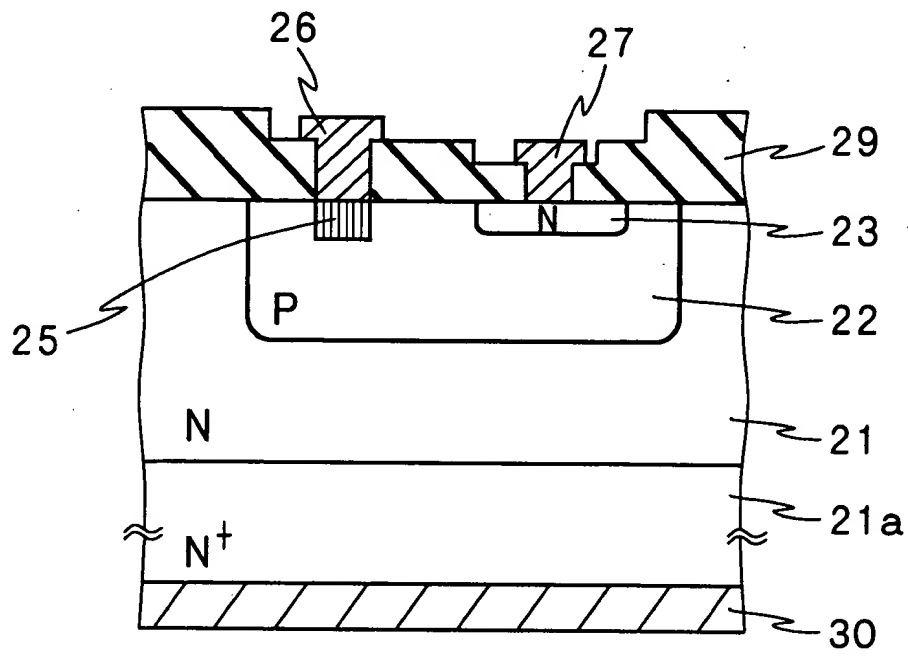


FIG. 2

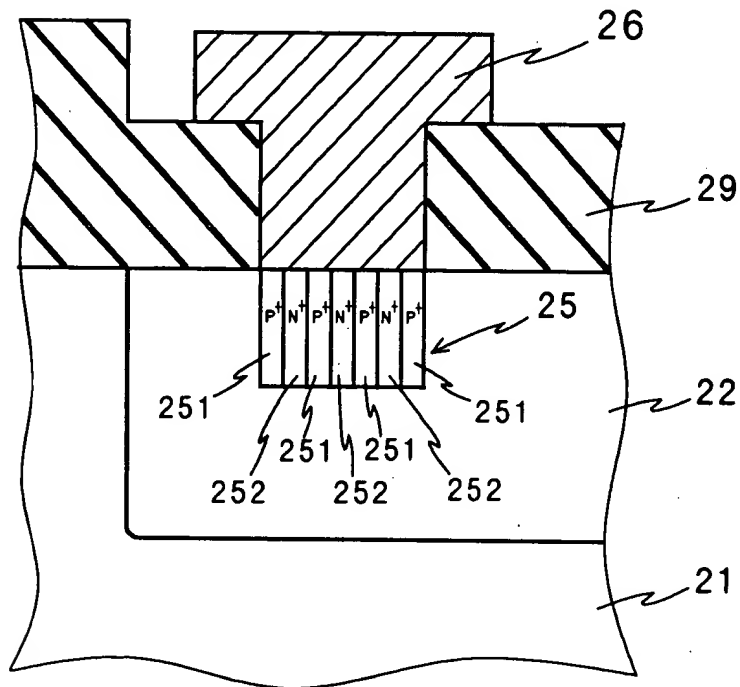


FIG. 3

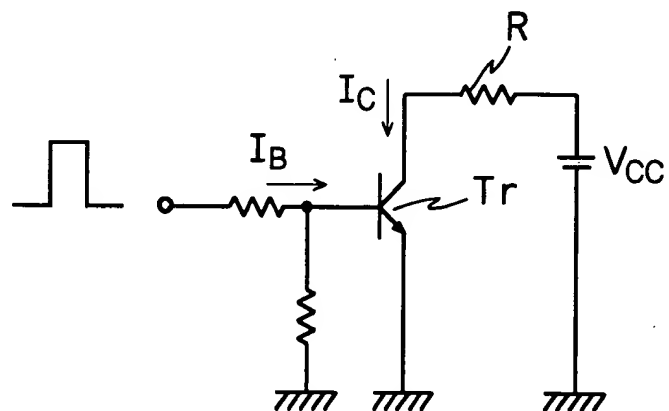


FIG. 4 (a)

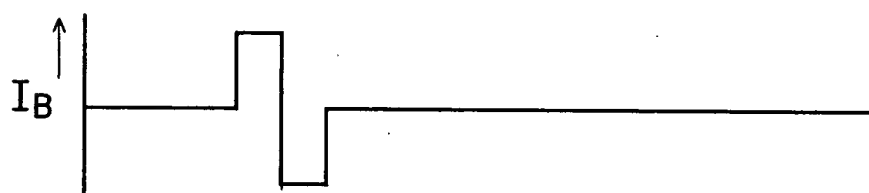


FIG. 4 (b)

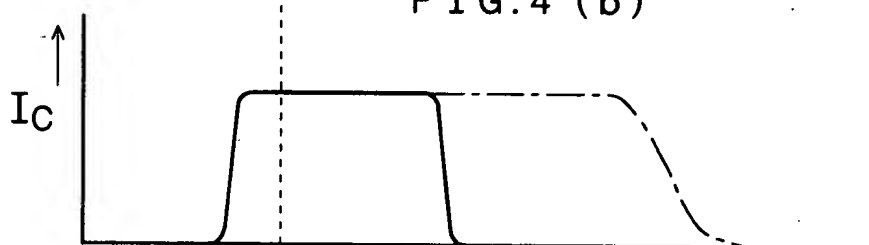


FIG. 4 (c)

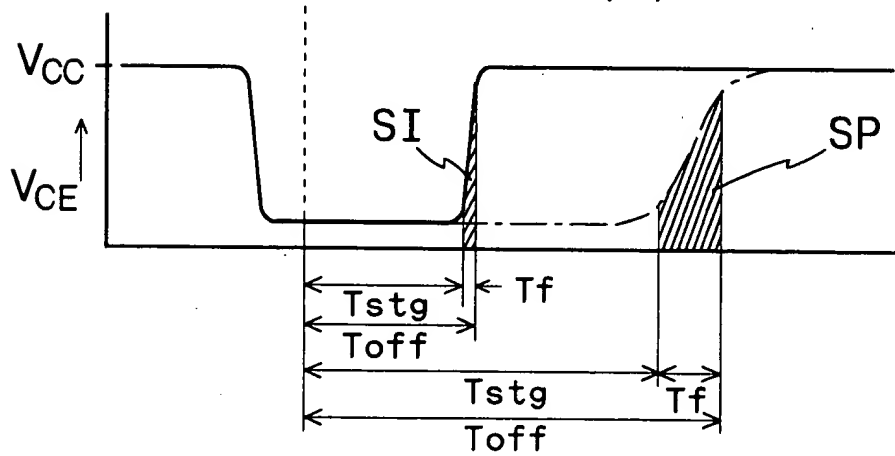
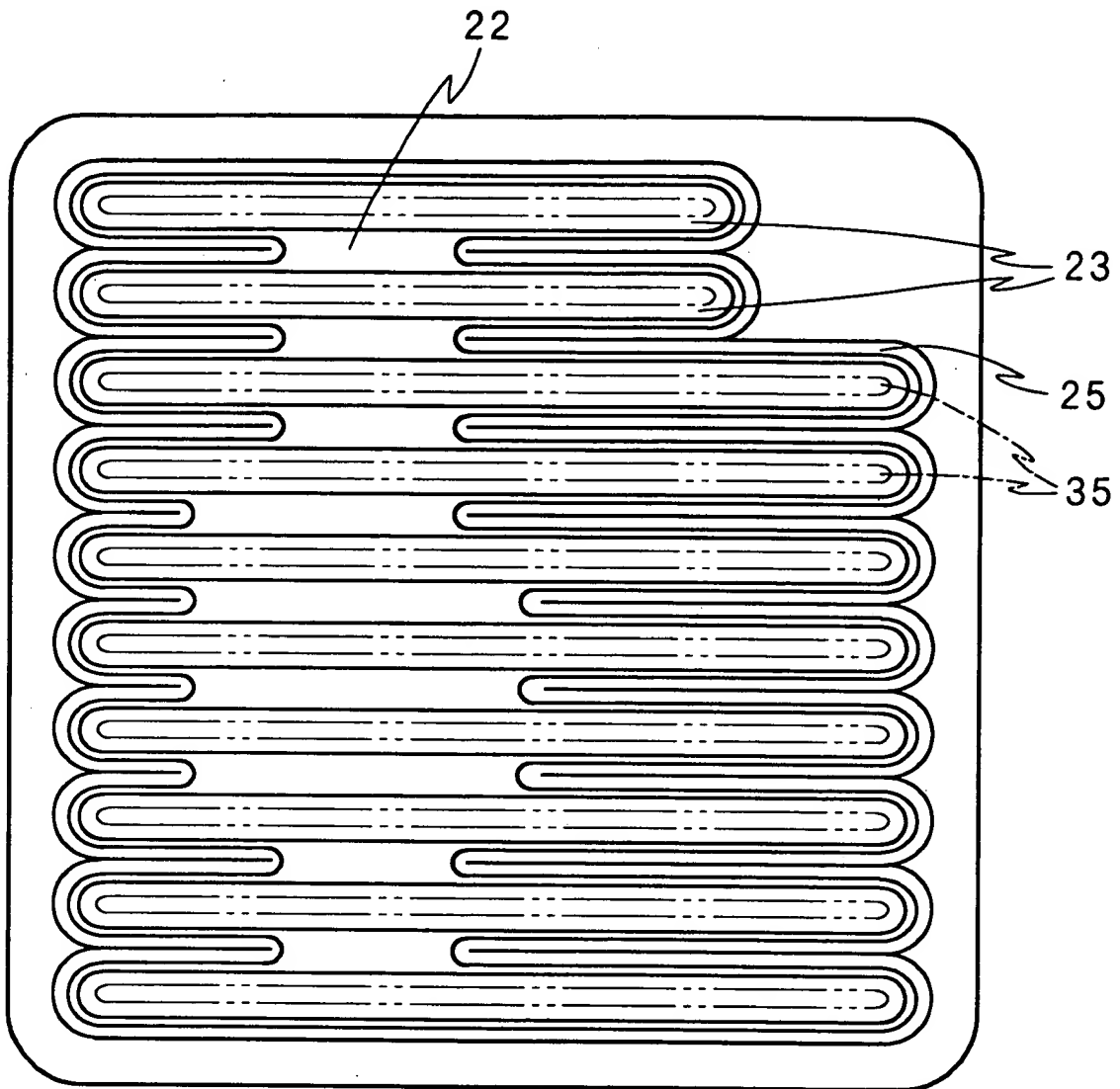


FIG. 5



09926425.103001

FIG. 6

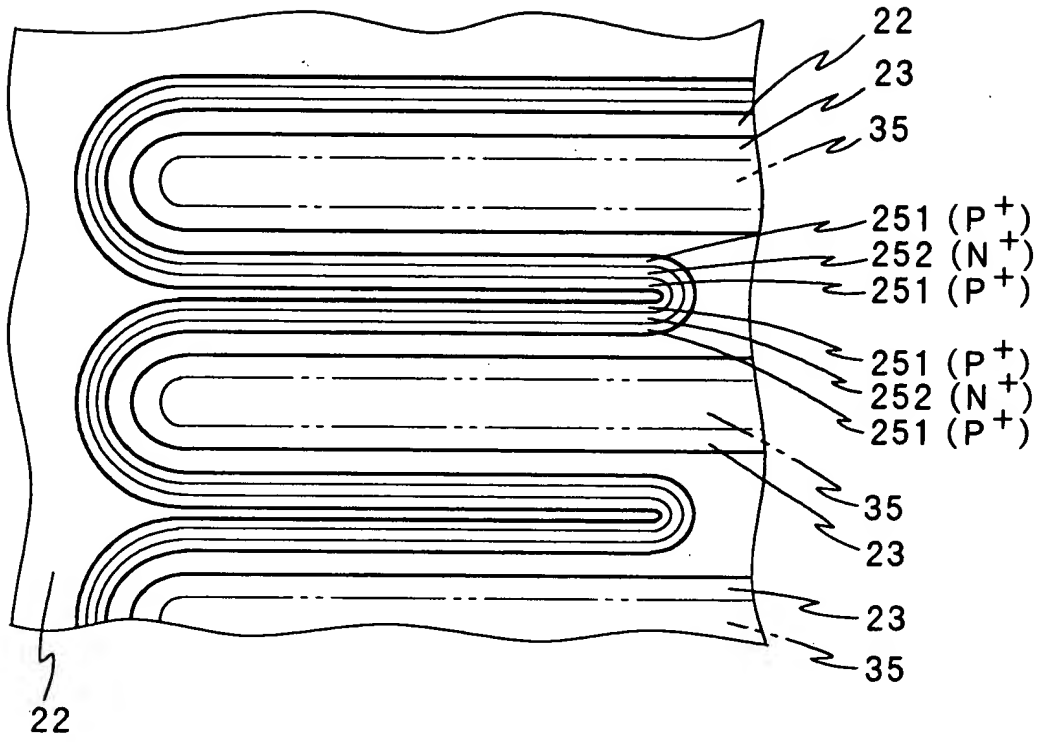


FIG. 6

FIG. 7

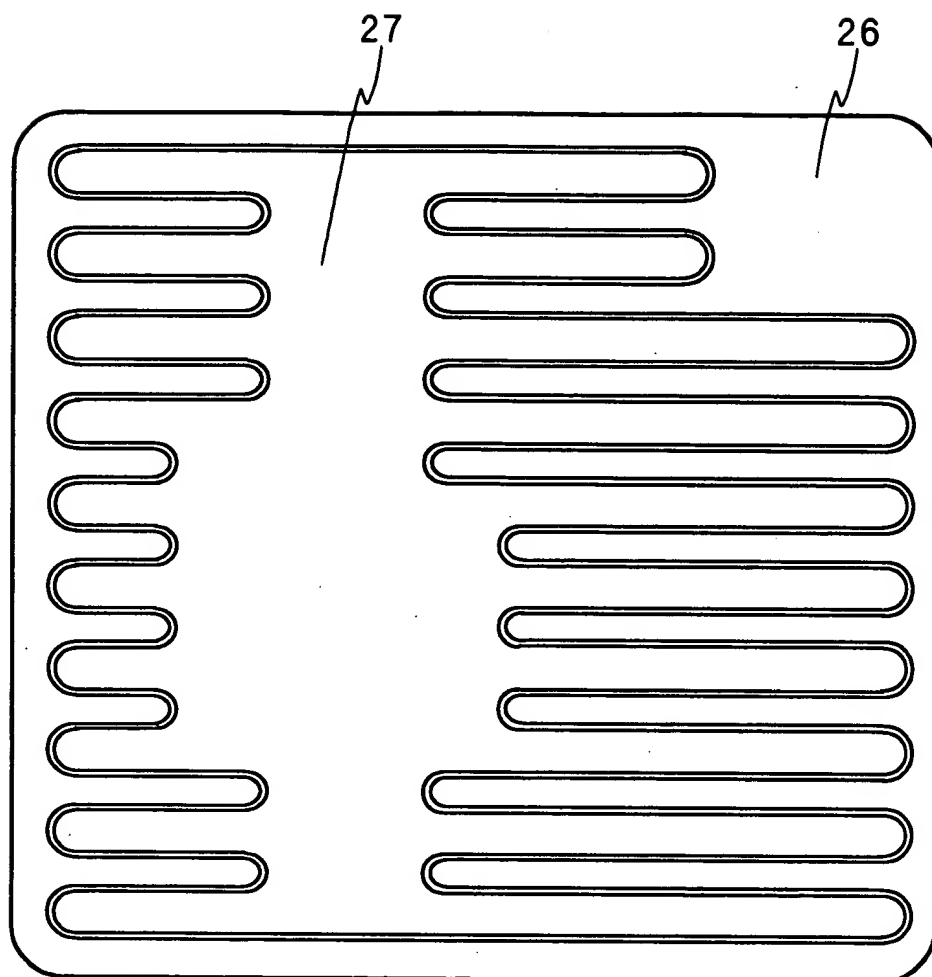
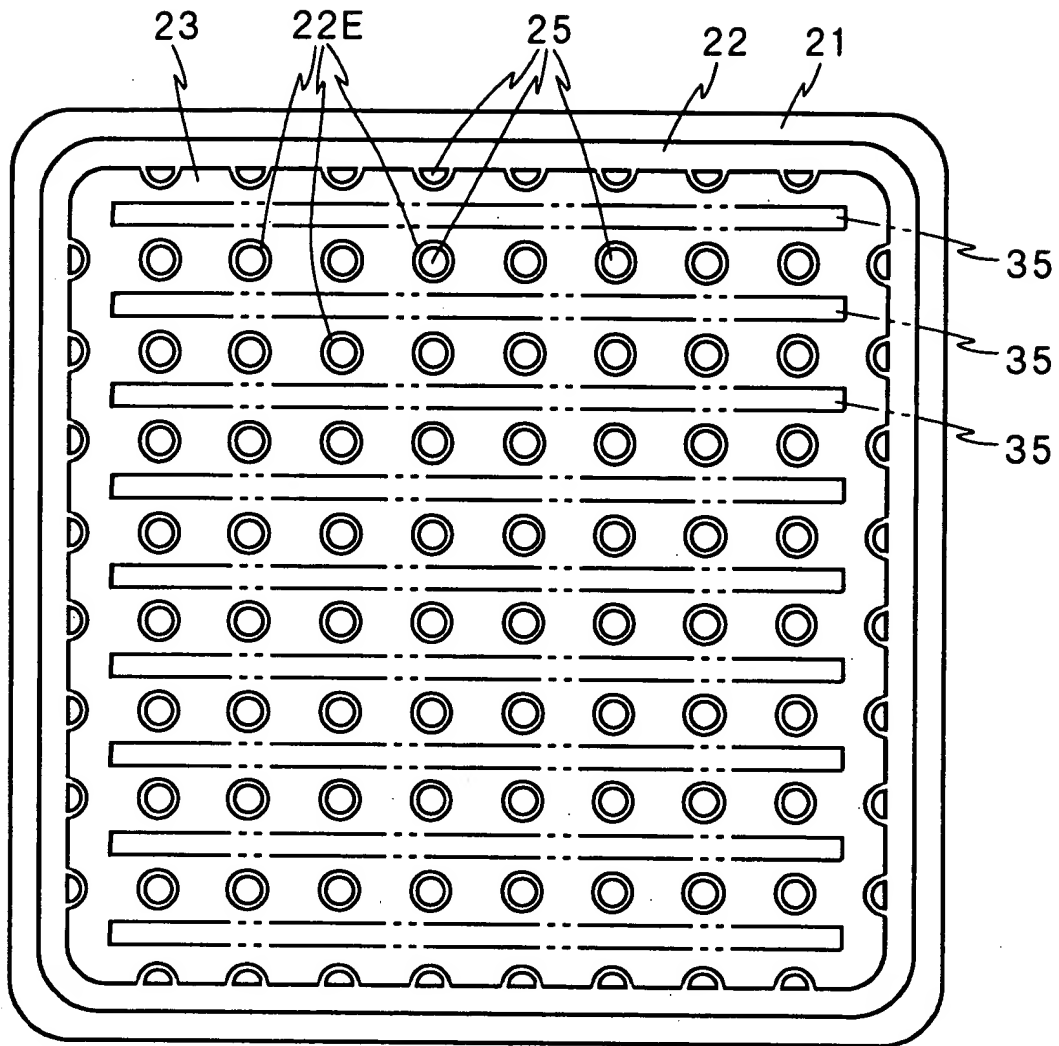


FIG. 7

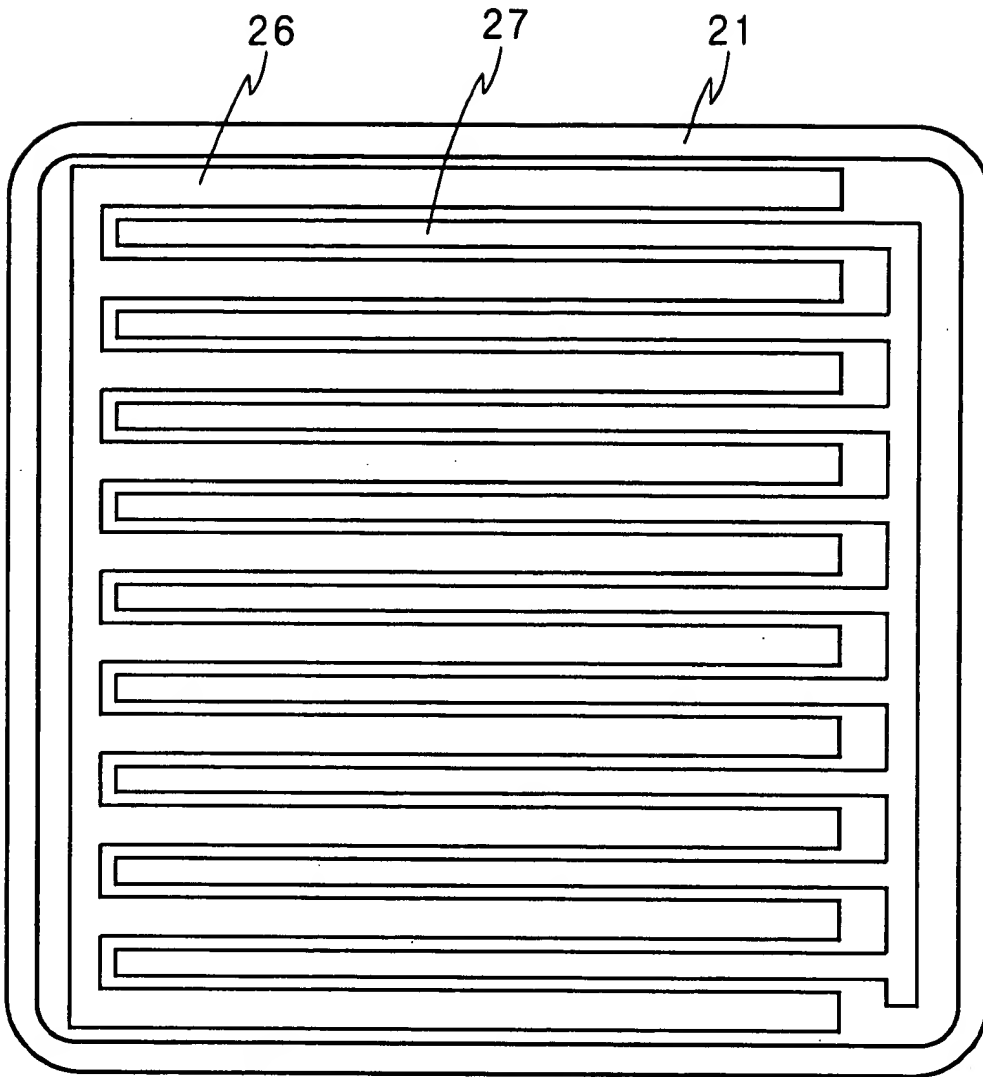
FIG. 8



T00E01-52492650

Diagram illustrating a semiconductor device structure. The device is divided into two main sections by a dashed line labeled 35. Each section contains two circular regions, labeled 22E. The top section shows the internal structure of these regions, with concentric circles labeled 251(P⁺) and 252(N⁺). The bottom section shows the external structure, with concentric circles labeled 25. The entire device is labeled 23.

FIG. 10



10996425-103004

FIG. 11

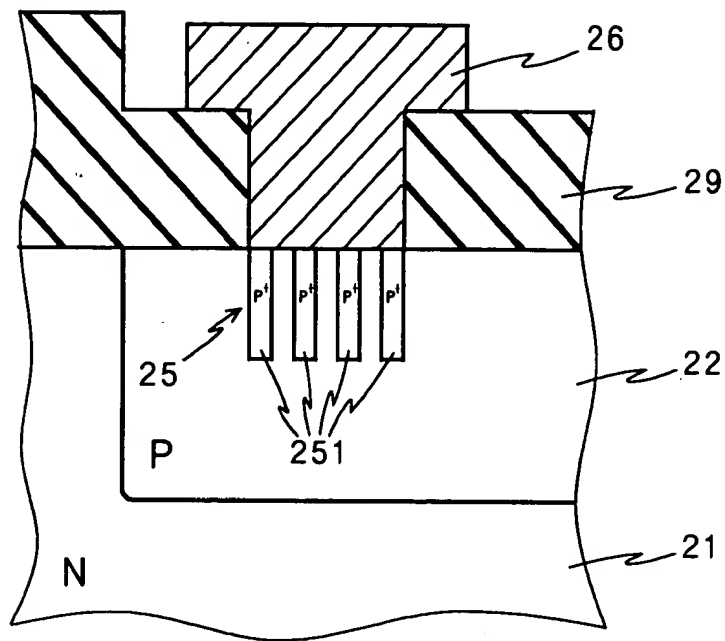


FIG. 12

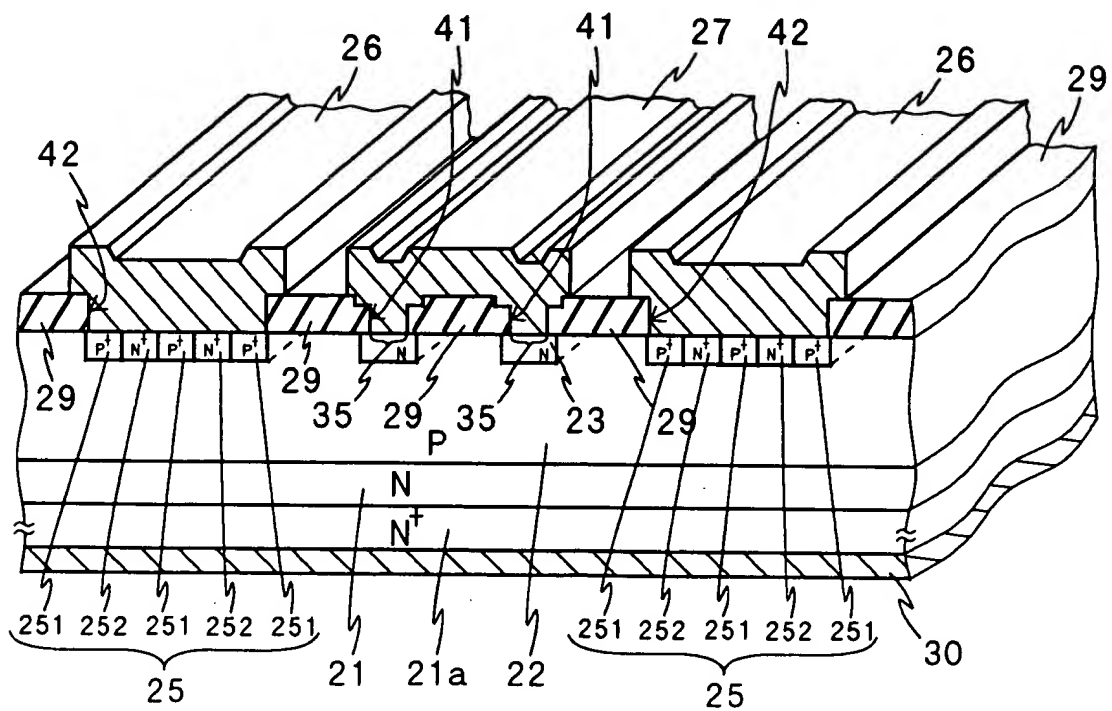
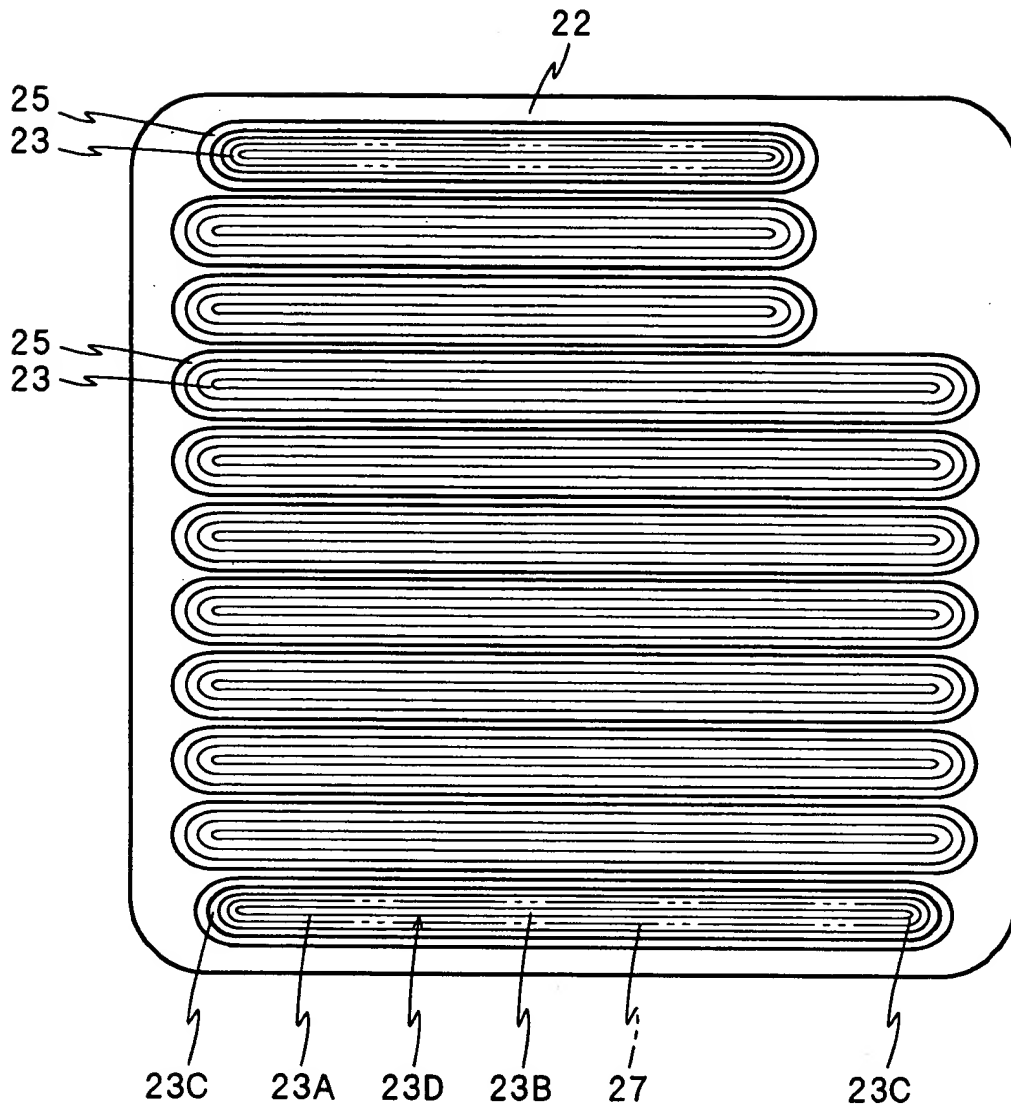


FIG. 13



09926425 "103001

FIG. 14

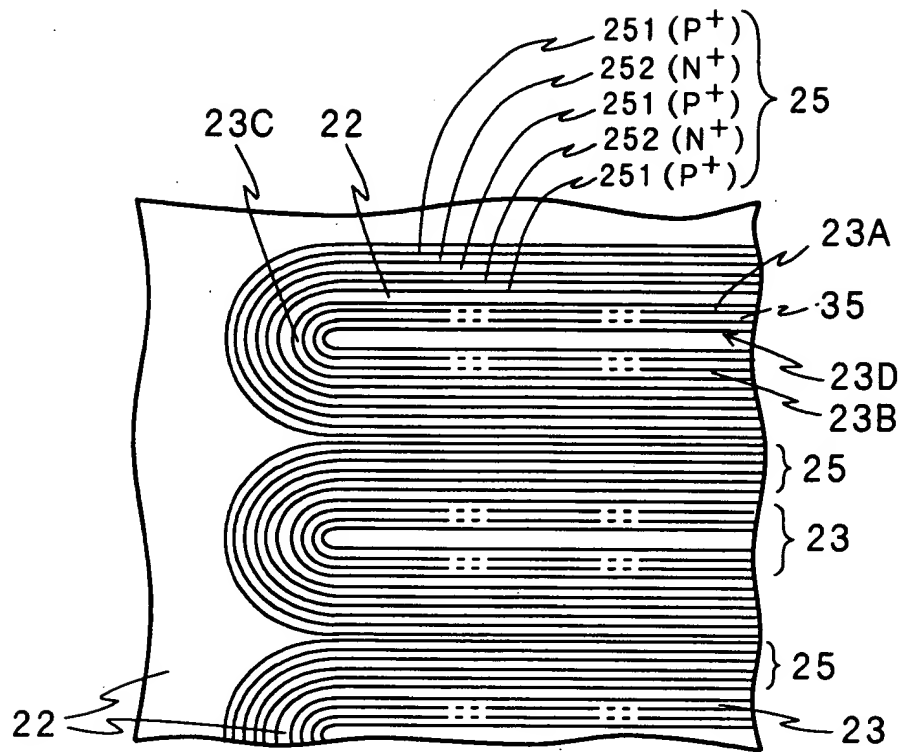


FIG. 15

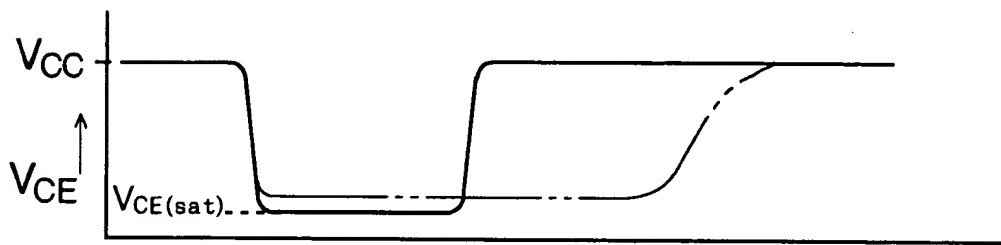


FIG. 16

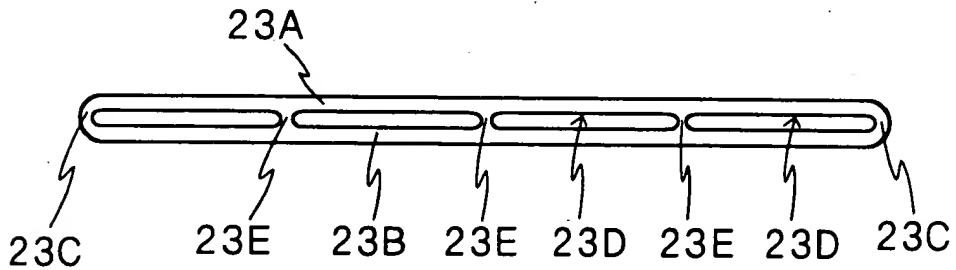


FIG. 17

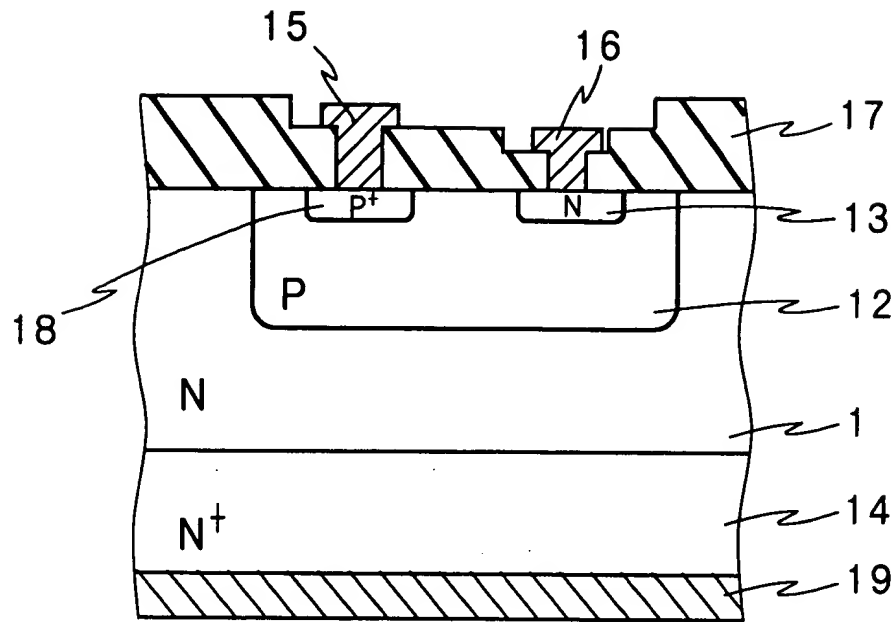


FIG. 18

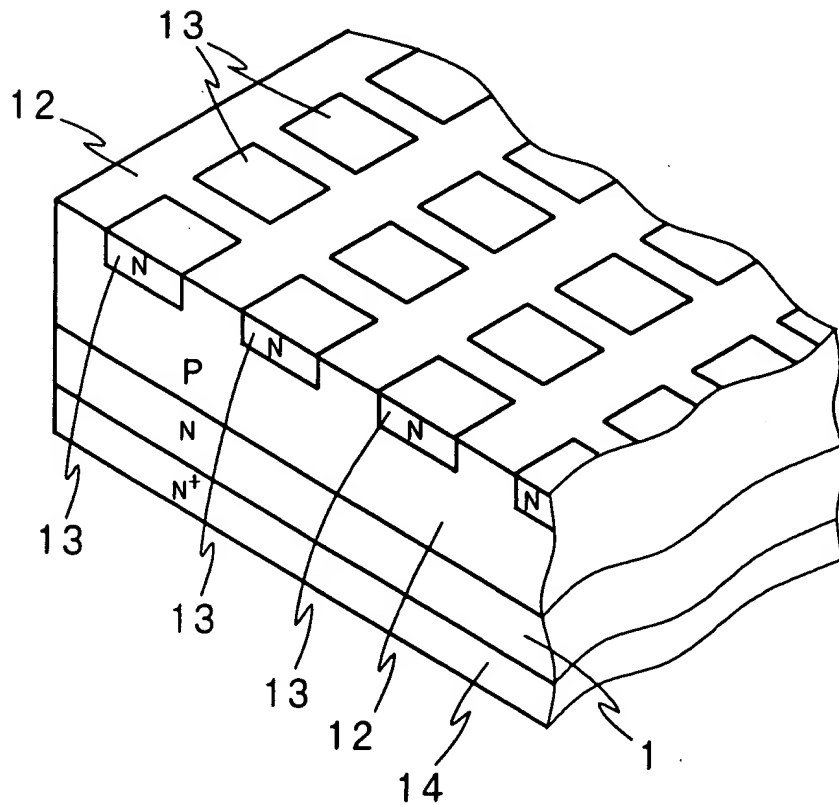


FIG. 19

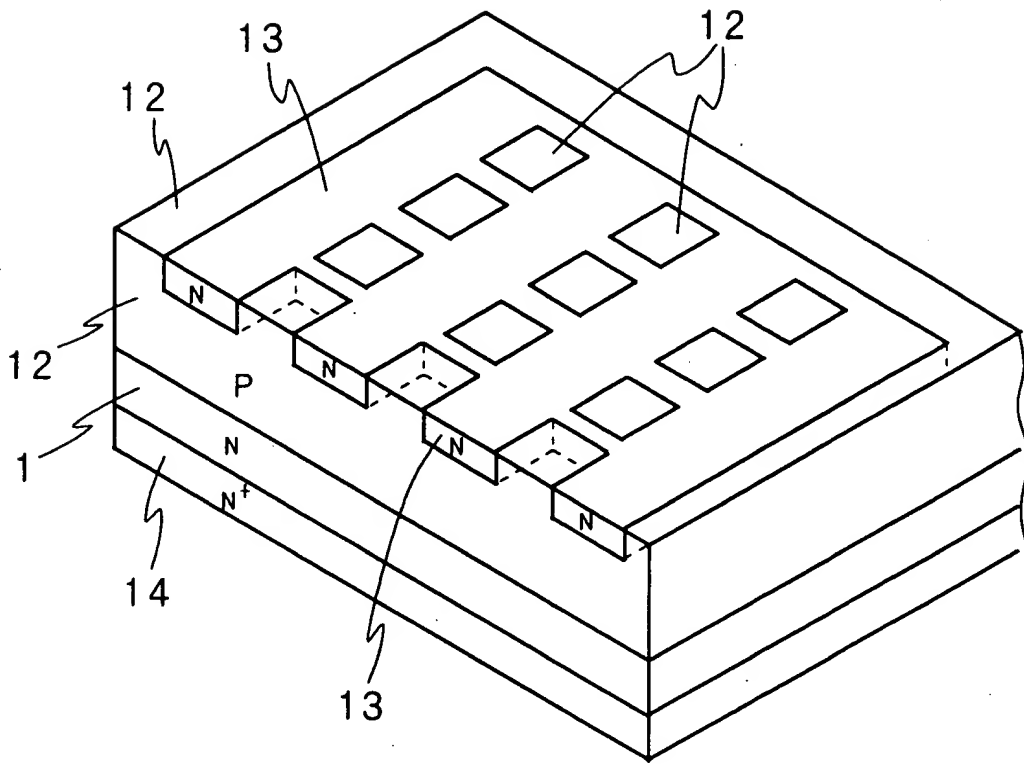


FIG. 20

